



# STGF30NC60S STGP30NC60S, STGWF30NC60S

30 A, 600 V, fast IGBT

## Features

- Optimized performance for medium operating frequencies up to 5 kHz in hard switching
- Low on-voltage drop ( $V_{CE(sat)}$ )
- High current capability

## Application

Motor drive

## Description

This device utilizes the advanced PowerMESH™ process resulting in an excellent trade-off between switching performance and low on-state behavior.

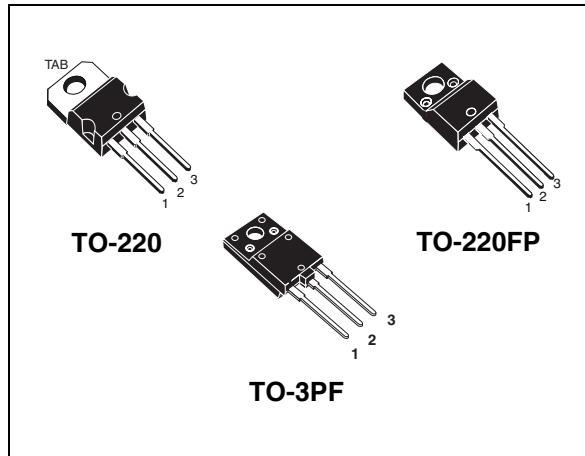


Figure 1. Internal schematic diagram

Table 1. Device summary

Part numbers	Marking	Package	Packaging
STGF30NC60S	GF30NC60S	TO-220FP	Tube
STGP30NC60S	GP30NC60S	TO-220	
STGWF30NC60S	GWF30NC60S	TO-3PF	

## Contents

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value			Unit
		TO-220	TO-220FP	TO-3PF	
$V_{CES}$	Collector-emitter voltage ( $V_{GE} = 0$ )		600		V
$I_C^{(1)}$	Continuous collector current at $T_C = 25^\circ\text{C}$	55	22	31	A
$I_C^{(1)}$	Continuous collector current at $T_C = 100^\circ\text{C}$	35	11	15	A
$I_{CL}^{(2)}$	Turn-off latching current		150		A
$I_{CP}^{(3)}$	Pulsed collector current		150		A
$V_{GE}$	Gate-emitter voltage		$\pm 20$		V
$V_{ISO}$	Insulation withstand voltage (RMS) from all three leads to external heat sink ( $t=1\text{ s}; T_C=25^\circ\text{C}$ )		2500		V
$P_{TOT}$	Total dissipation at $T_C = 25^\circ\text{C}$	175	40	62.5	W
$T_j$	Operating junction temperature	- 55 to 150			$^\circ\text{C}$

1. Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{j(\max)} - T_C}{R_{thj-c} \times V_{CE(sat)(max)}(T_{j(\max)}, I_C(T_C))}$$

2.  $V_{clamp} = 80\% \cdot (V_{CES})$ ,  $T_j = 150^\circ\text{C}$ ,  $R_G = 10\ \Omega$ ,  $V_{GE} = 15\text{ V}$

3. Pulse width limited by maximum junction temperature and turn-off within RBSOA

**Table 3. Thermal data**

Symbol	Parameter	Value			Unit
		TO-220	TO-220FP	TO-3PF	
$R_{thj-case}$	Thermal resistance junction-case	0.7	3.1	2	$^\circ\text{C/W}$
$R_{thj-amb}$	Thermal resistance junction-ambient		62.5	50	$^\circ\text{C/W}$

## 2 Electrical characteristics

( $T_J = 25^\circ\text{C}$  unless otherwise specified)

**Table 4. Static**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(\text{BR})\text{CES}}$	Collector-emitter breakdown voltage ( $V_{GE} = 0$ )	$I_C = 1 \text{ mA}$	600			V
$V_{CE(\text{sat})}$	Collector-emitter saturation voltage	$V_{GE} = 15 \text{ V}, I_C = 20 \text{ A}$ $V_{GE} = 15 \text{ V}, I_C = 20 \text{ A}, T_J = 150^\circ\text{C}$		1.5 1.4	1.9	V V
$V_{GE(\text{th})}$	Gate threshold voltage	$V_{CE} = V_{GE}, I_C = 250 \mu\text{A}$	3.75		5.75	V
$I_{CES}$	Collector cut-off current ( $V_{GE} = 0$ )	$V_{CE} = 600 \text{ V}$ $V_{CE} = 600 \text{ V}, T_J = 150^\circ\text{C}$			150 1	$\mu\text{A}$ mA
$I_{GES}$	Gate-emitter cut-off current ( $V_{CE} = 0$ )	$V_{GE} = \pm 20 \text{ V}$			$\pm 100$	nA
$g_{fs}^{(1)}$	Forward transconductance	$V_{CE} = 15 \text{ V}, I_C = 20 \text{ A}$		10		S

1. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{ies}$	Input capacitance			2200		pF
$C_{oes}$	Output capacitance		-	185	-	pF
$C_{res}$	Reverse transfer capacitance	$V_{CE} = 25 \text{ V}, f = 1 \text{ MHz}, V_{GE} = 0$		48.5		pF
$Q_g$	Total gate charge			96		nC
$Q_{ge}$	Gate-emitter charge	$V_{CE} = 480 \text{ V}, I_C = 20 \text{ A},$ $V_{GE} = 15 \text{ V}$	-	14	-	nC
$Q_{gc}$	Gate-collector charge	<a href="#">Figure 19</a>		44.5		nC

**Table 6. Switching on/off (inductive load)**

<b>Symbol</b>	<b>Parameter</b>	<b>Test conditions</b>	<b>Min.</b>	<b>Typ.</b>	<b>Max.</b>	<b>Unit</b>
$t_{d(on)}$ $t_r$ ( $di/dt$ ) <sub>on</sub>	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 480 \text{ V}$ , $I_C = 20 \text{ A}$ $R_G = 10 \Omega$ , $V_{GE} = 15 \text{ V}$ <i>Figure 18</i>	-	21.5 8.5 2280	-	ns ns A/ $\mu\text{s}$
$t_{d(on)}$ $t_r$ ( $di/dt$ ) <sub>on</sub>	Turn-on delay time Current rise time Turn-on current slope	$V_{CC} = 480 \text{ V}$ , $I_C = 20 \text{ A}$ $R_G = 10 \Omega$ , $V_{GE} = 15 \text{ V}$ , $T_J = 125^\circ\text{C}$ <i>Figure 18</i>	-	20.5 9.5 2150	-	ns ns A/ $\mu\text{s}$
$t_r(V_{off})$ $t_d(off)$ $t_f$	Off voltage rise time Turn-off delay time Current fall time	$V_{cc} = 480 \text{ V}$ , $I_C = 20 \text{ A}$ , $R_{GE} = 10 \Omega$ , $V_{GE} = 15 \text{ V}$ <i>Figure 18</i>	-	85 180 200	-	ns ns ns
$t_r(V_{off})$ $t_d(off)$ $t_f$	Off voltage rise time Turn-off delay time Current fall time	$V_{cc} = 480 \text{ V}$ , $I_C = 20 \text{ A}$ , $R_{GE} = 10 \Omega$ , $V_{GE} = 15 \text{ V}$ $T_J = 125^\circ\text{C}$ <i>Figure 18</i>	-	155 260 295	-	ns ns ns

**Table 7. Switching energy (inductive load)**

<b>Symbol</b>	<b>Parameter</b>	<b>Test conditions</b>	<b>Min.</b>	<b>Typ.</b>	<b>Max.</b>	<b>Unit</b>
$E_{on}$ $E_{off}^{(1)}$ $E_{ts}$	Turn-on switching losses Turn-off switching losses Total switching losses	$V_{CC} = 480 \text{ V}$ , $I_C = 20 \text{ A}$ $R_G = 10 \Omega$ , $V_{GE} = 15 \text{ V}$ , <i>Figure 18</i>	-	300 1275 1575	-	$\mu\text{J}$ $\mu\text{J}$ $\mu\text{J}$
$E_{on}$ $E_{off}^{(1)}$ $E_{ts}$	Turn-on switching losses Turn-off switching losses Total switching losses	$V_{CC} = 480 \text{ V}$ , $I_C = 20 \text{ A}$ $R_G = 10 \Omega$ , $V_{GE} = 15 \text{ V}$ , $T_J = 125^\circ\text{C}$ <i>Figure 18</i>	-	430 1965 2395	-	$\mu\text{J}$ $\mu\text{J}$ $\mu\text{J}$

1. Turn-off losses include also the tail of the collector current.

## 2.1 Electrical characteristics (curves)

Figure 2. Output characteristics

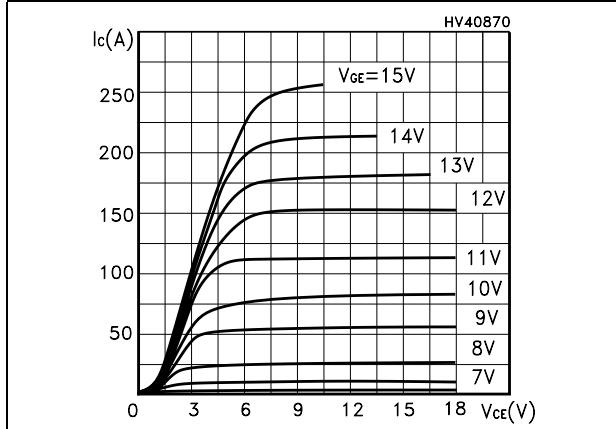


Figure 3. Transfer characteristics

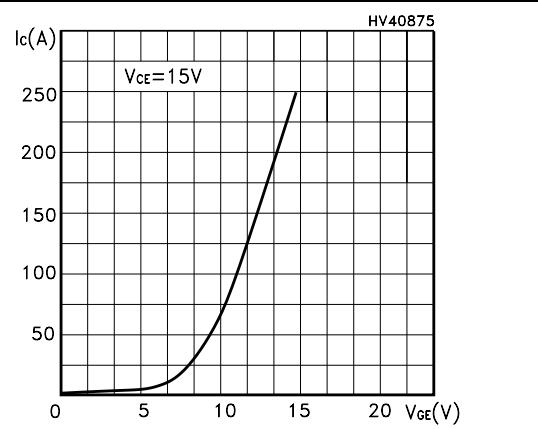


Figure 4. Transconductance

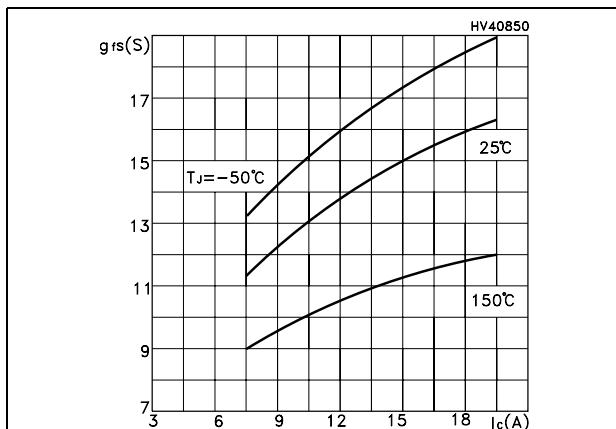


Figure 5. Collector-emitter on voltage vs temperature

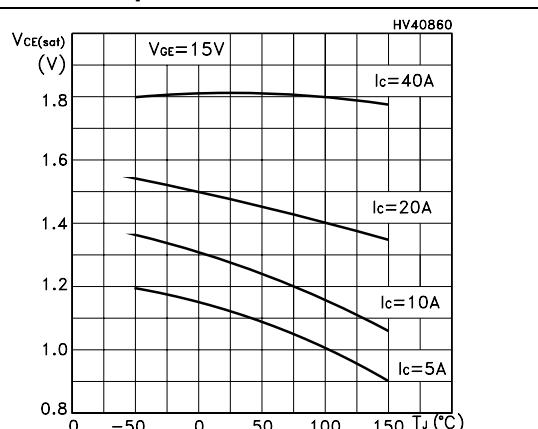


Figure 6. Gate charge vs gate-source voltage

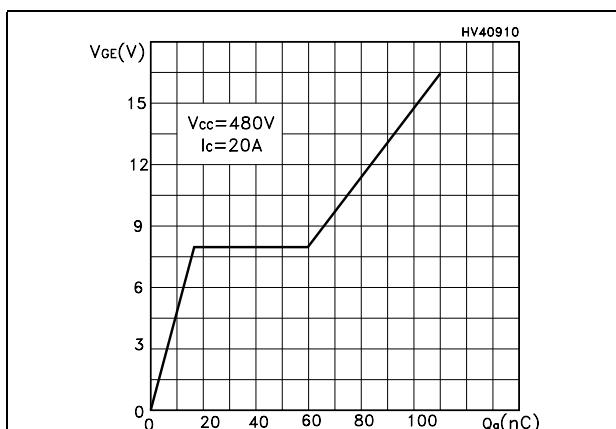
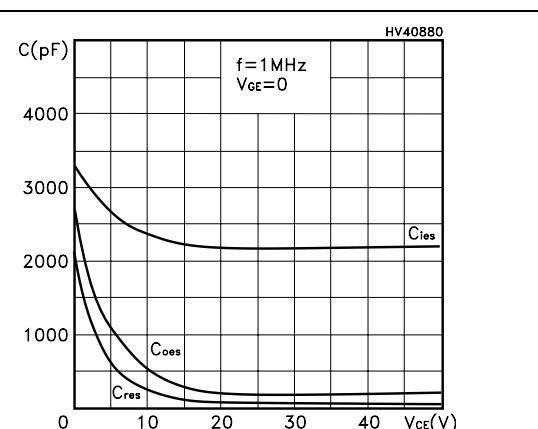


Figure 7. Capacitance variations



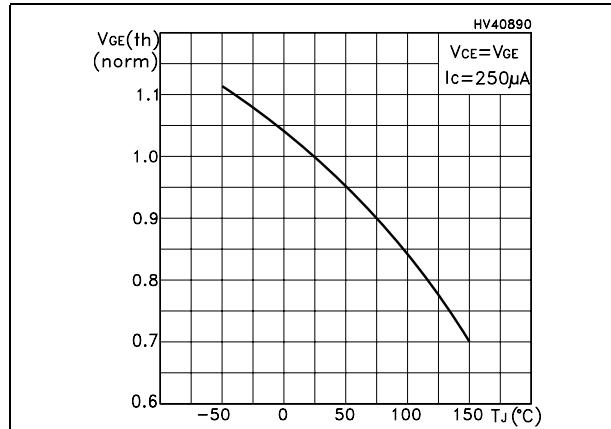
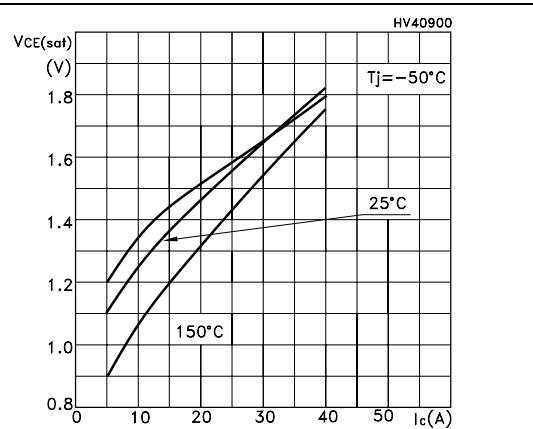
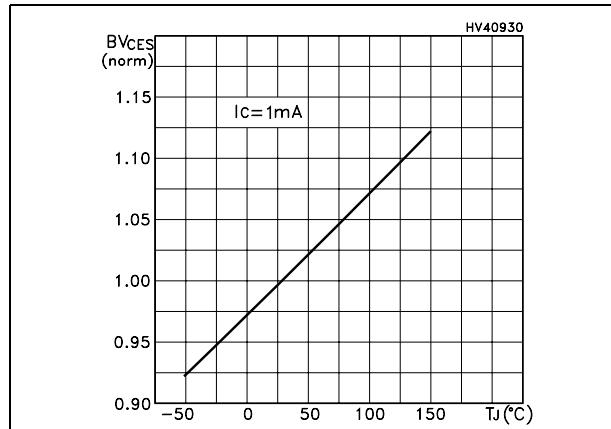
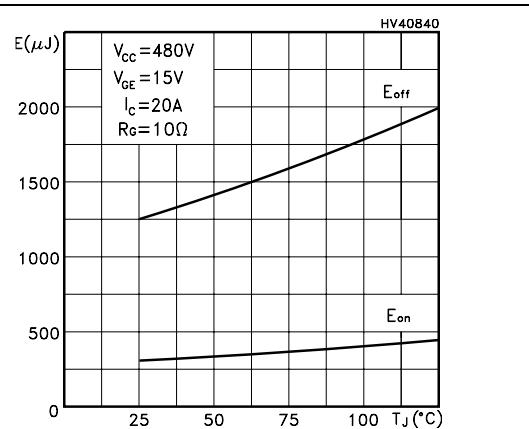
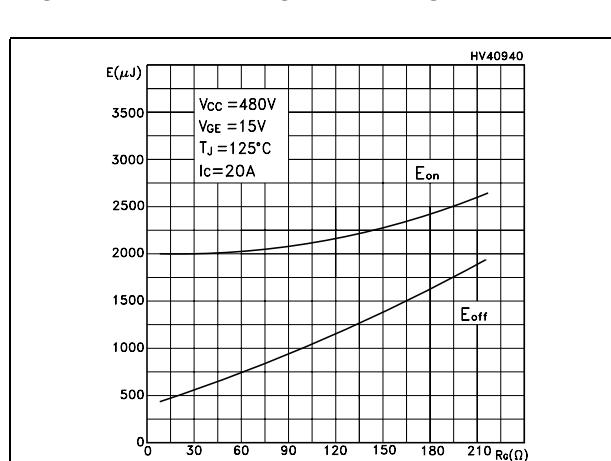
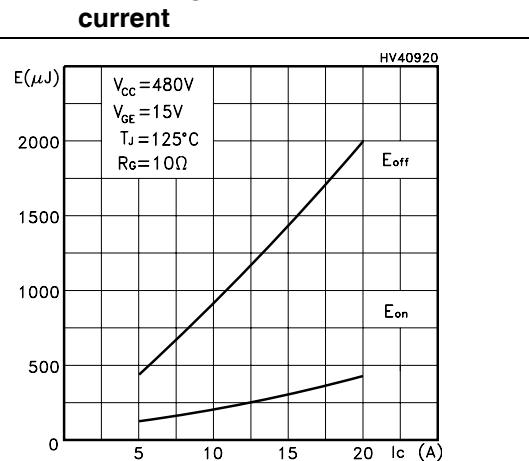
**Figure 8. Normalized gate threshold voltage vs temperature****Figure 9. Collector-emitter on voltage vs collector current****Figure 10. Normalized breakdown voltage vs temperature****Figure 11. Switching losses vs temperature****Figure 12. Switching losses vs gate resistance****Figure 13. Switching losses vs collector current**

Figure 14. Thermal Impedance

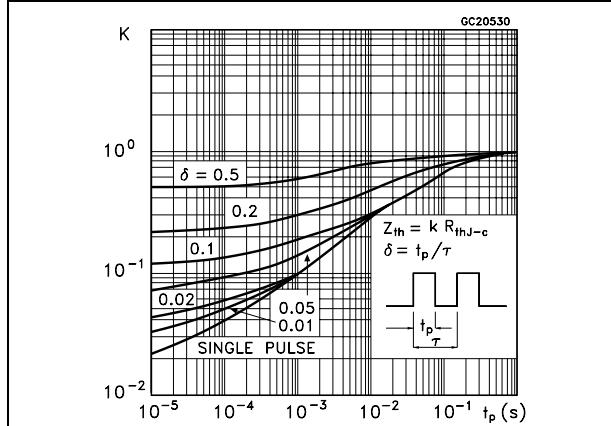


Figure 15. Turn-off SOA

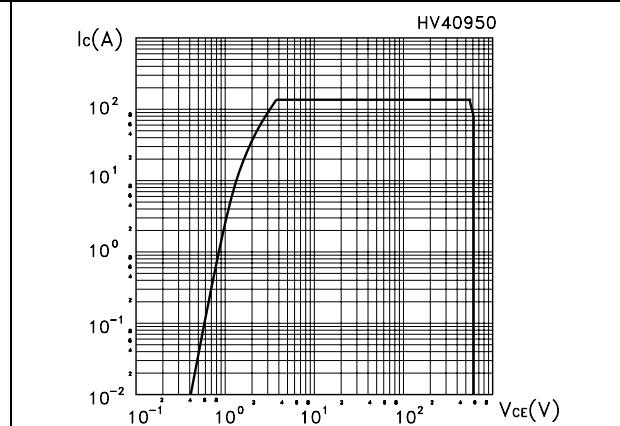


Figure 16. Thermal Impedance for TO-220FP

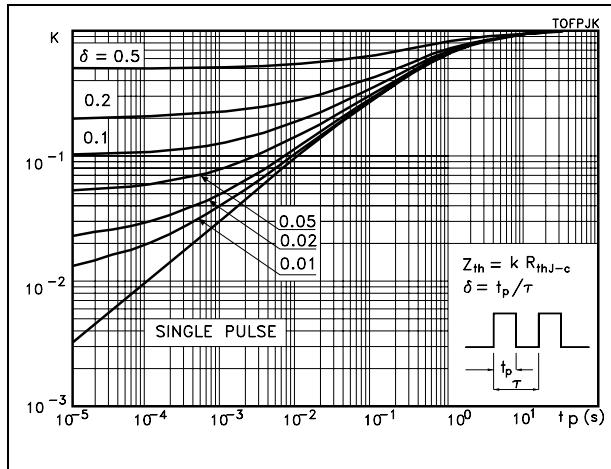
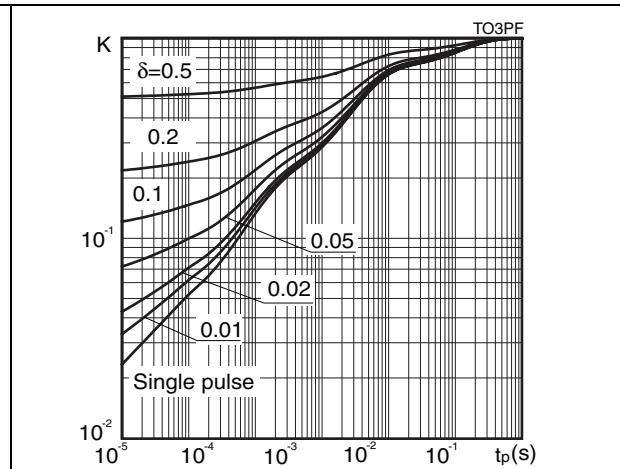
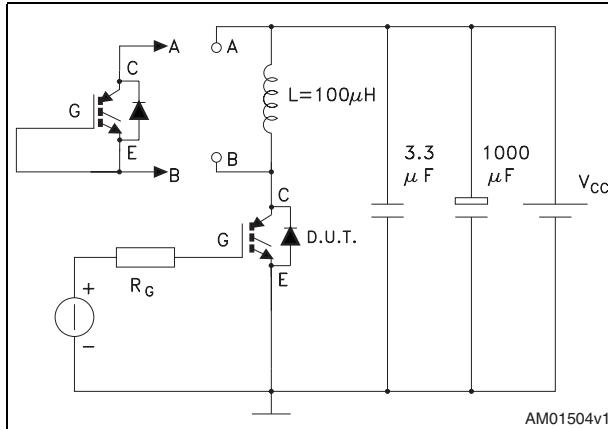


Figure 17. Thermal Impedance for TO-3PF

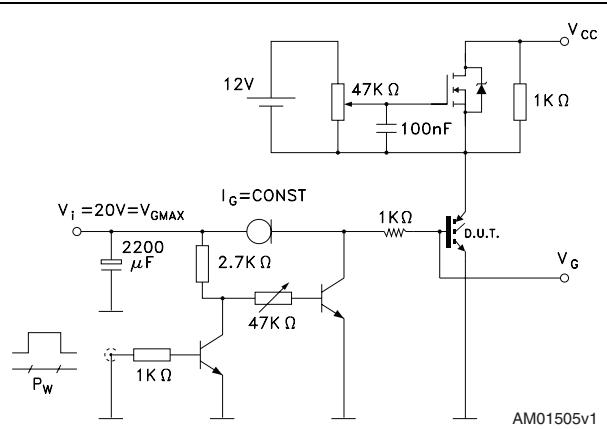


### 3 Test circuits

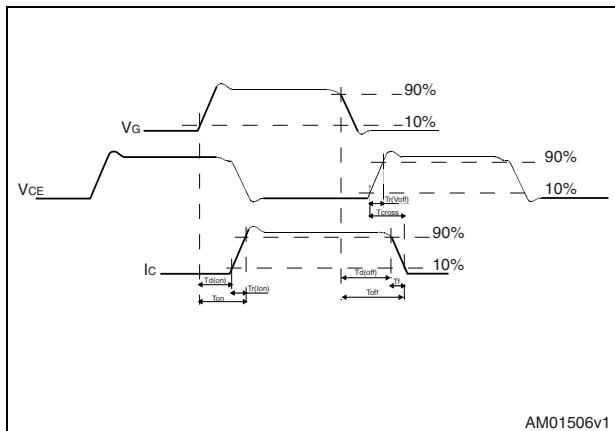
**Figure 18. Test circuit for inductive load switching**



**Figure 19. Gate charge test circuit**



**Figure 20. Switching waveforms**

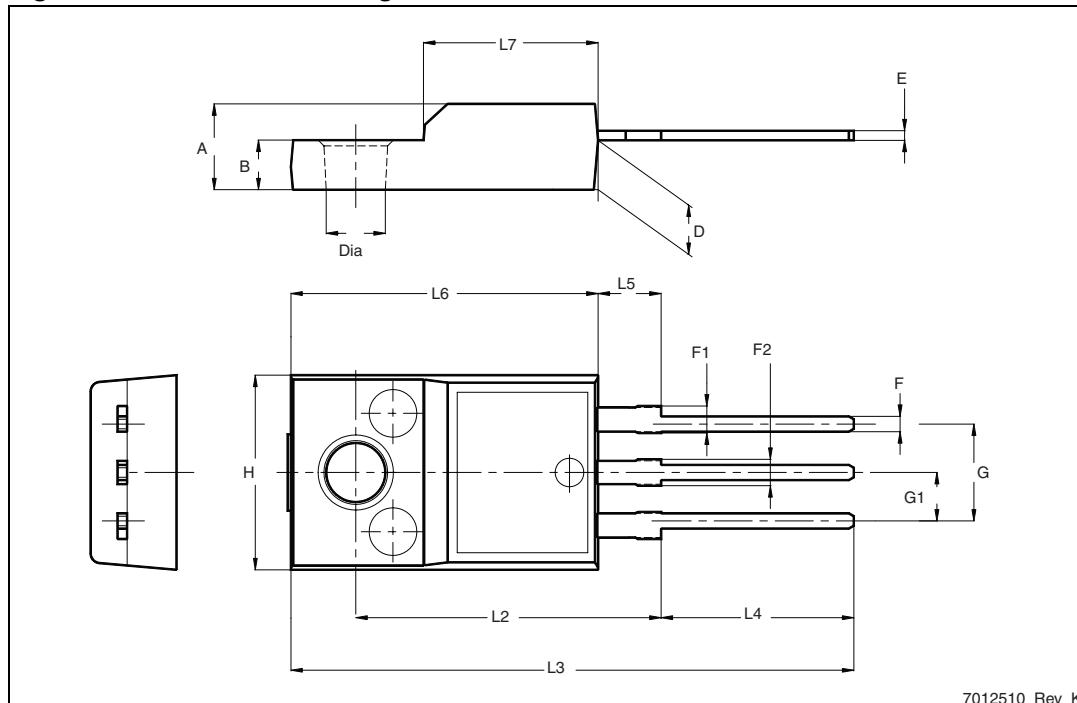


## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

**Table 8.** TO-220FP mechanical data

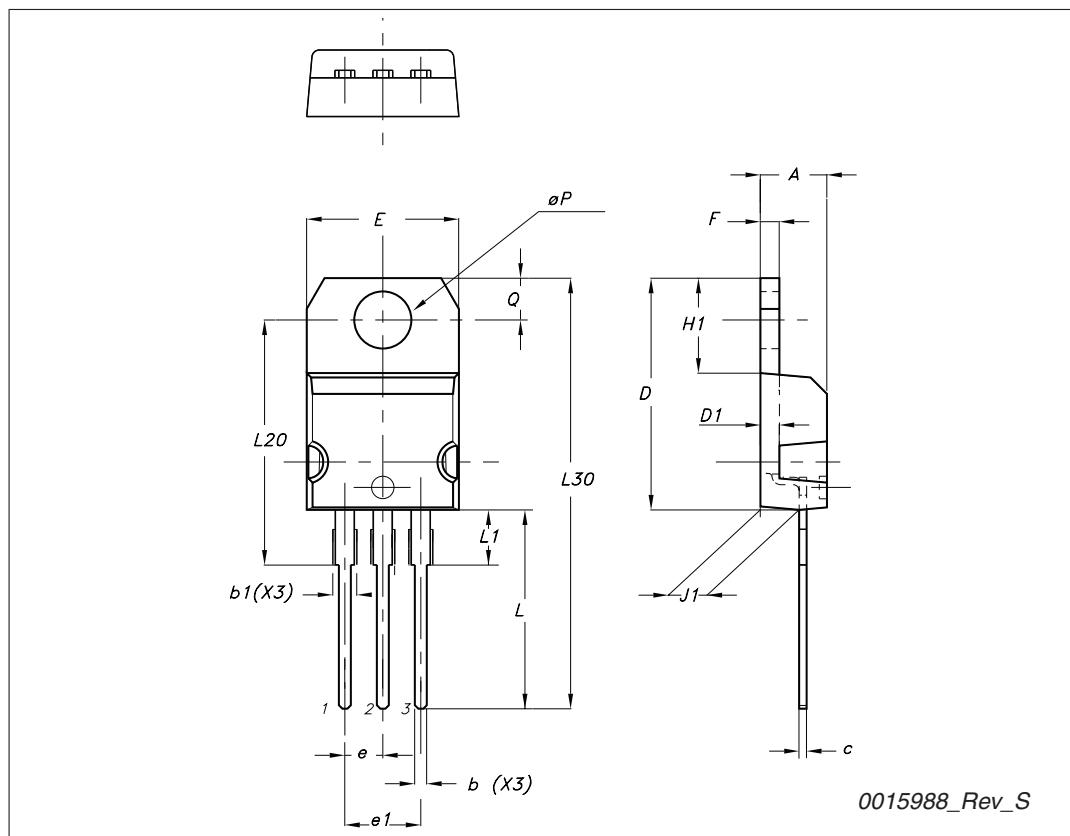
Dim.	mm		
	Min.	Typ.	Max.
A	4.4		4.6
B	2.5		2.7
D	2.5		2.75
E	0.45		0.7
F	0.75		1
F1	1.15		1.70
F2	1.15		1.70
G	4.95		5.2
G1	2.4		2.7
H	10		10.4
L2		16	
L3	28.6		30.6
L4	9.8		10.6
L5	2.9		3.6
L6	15.9		16.4
L7	9		9.3
Dia	3		3.2

**Figure 21.** TO-220FP drawing

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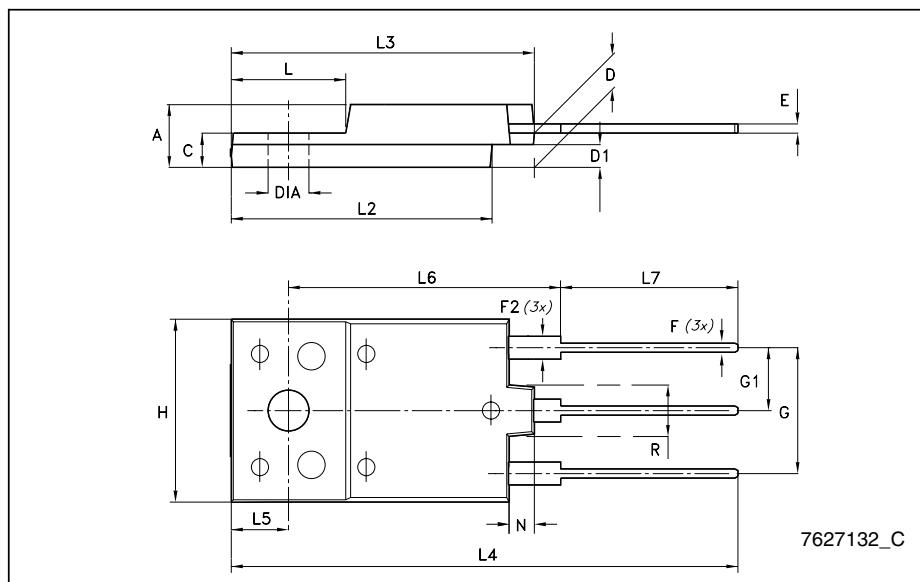
## TO-220 type A mechanical data

Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
$\emptyset P$	3.75		3.85
Q	2.65		2.95



## TO-3PF mechanical data

DIM.	mm.		
	min.	typ	max.
A	5.30		5.70
C	2.80		3.20
D	3.10		3.50
D1	1.80		2.20
E	0.80		1.10
F	0.65		0.95
F2	1.80		2.20
G	10.30		11.50
G1		5.45	
H	15.30		15.70
L	9.80	10	10.20
L2	22.80		23.20
L3	26.30		26.70
L4	43.20		44.40
L5	4.30		4.70
L6	24.30		24.70
L7	14.60		15
N	1.80		2.20
R	3.80		4.20
Dia	3.40		3.80



## 5 Revision history

**Table 9. Document revision history**

Date	Revision	Changes
02-Jul-2007	1	Initial release
20-Nov-2007	2	Document status promoted from preliminary data to datasheet
04-May-2009	3	Added new package, mechanical data: TO-220FP
30-Jun-2010	4	Added new package, mechanical data: TO-3PF

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